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#### 100V P-CHANNEL ENHANCEMENT MODE MOSFET

### **Product Summary**

BV <sub>DSS</sub>	Max R <sub>DS(ON)</sub>	Max I <sub>D</sub> T <sub>A</sub> = +25°C		
-100V	1.0Ω @ V <sub>GS</sub> = -10V	-0.7A		
	1.45Ω @ V <sub>GS</sub> = -6.0V	-0.5A		

### **Description and Applications**

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- DC-DC Converters
- Power Management Functions
- Disconnect Switches
- Motor Control

## **Features and Benefits**

- Fast Switching Speed
- Low Input Capacitance
- Low Gate Charge
- Low Threshold
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

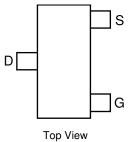
### **Mechanical Data**

- Case: SOT23 (Type DN)
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
   Solderable per MIL-STD-202, Method 208 <sup>®</sup>3
- Weight: 0.009 grams (Approximate)

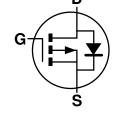




Top View



Pin Out



Equivalent Circuit

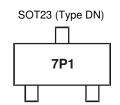
### **Ordering Information** (Note 5)

Part Number	Case	Packaging
ZXMP10A13FQTA	SOT23 (Type DN)	3000/Tape & Reel
ZXMP10A13FQTC	SOT23 (Type DN)	10,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/product-compliance-definitions/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

## **Marking Information**



7P1 = Product Type Marking Code



# **Maximum Ratings** $(@T_A = +25^{\circ}C, \text{ unless otherwise specified.})$

Characteristic			Symbol	Value	Unit	
Drain-Source Voltage			$V_{DSS}$	-100	V	
Gate-Source Voltage			V <sub>GS</sub>	±20	V	
Continuous Drain Current	V <sub>GS</sub> = -10V	T <sub>A</sub> = +70°C	(Note 7) (Note 7) (Note 7)	I <sub>D</sub>	-0.7 -0.5 -0.6	А
Pulsed Drain Current (Note 8)			I <sub>DM</sub>	-3.1	Α	
Continuous Source Current (Body Diode) (Note 6)			Is	-1.1	A	
Pulsed Source Current (Body Diode) (Note 8)			I <sub>SM</sub>	-3.1	A	

## **Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Linear Derating Factor	P <sub>D</sub>	625 5	mW mW/°C
Power Dissipation (Note 7) Linear Derating Factor	P <sub>D</sub>	806 6.4	mW mW/°C
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	200	°C/W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	155	°C/W
Thermal Resistance, Junction to Leads (Note 9)	R <sub>0JL</sub>	194	°C/W
Operating and Storage Temperature Range	$T_{J_i}T_{STG}$	-55 to +150	°C

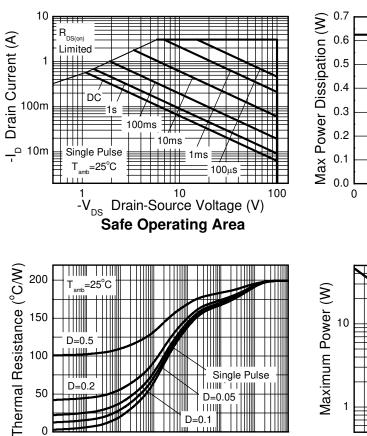
Notes:

- 6. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
  7. For a device surface mounted on FR-4 PCB measured at t ≤ 5 secs.
  8. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05 pulse width = 10µs pulse current limited by maximum junction temperature.
  9. Thermal resistance from junction to solder-point (at the end of the drain lead).



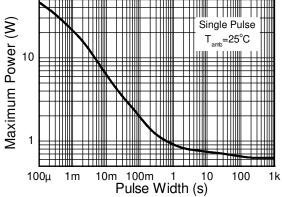
## **Thermal Characteristics**

50



60 80 100 120 Temperature (°C) 20 140 160

**Derating Curve** 



**Transient Thermal Impedance** 

10m 100m 1 1 Pulse Width (s)

10

**Pulse Power Dissipation** 



# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-100	_	_	V	$I_D = -250 \mu A, V_{GS} = 0 V$	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	_	_	-1.0	μΑ	V <sub>DS</sub> = -100V, V <sub>GS</sub> = 0V	
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-2.0		-4.0	V	$I_D = -250 \mu A, \ V_{DS} = V_{GS}$	
Static Drain Source On Resistance (Note 10)	J			1.0	0	$V_{GS} = -10V, I_D = -0.6A$	
Static Drain-Source On-Resistance (Note 10)	R <sub>DS(ON)</sub>		_	1.45	Ω	$V_{GS} = -6.0V$ , $I_D = -0.5A$	
Forward Transconductance (Notes 10 and 12)	9fs	_	1.2	_	S	$V_{DS} = -15V, I_D = -0.6A$	
Diode Forward Voltage (Note 10)	V <sub>SD</sub>	_	-0.85	-0.95	V	$T_J = +25$ °C, $I_S = -0.75$ A, $V_{GS} = 0$ V	
Reverse Recovery Time (Note 12)	t <sub>RR</sub>	_	29	_	ns	$T_J = +25^{\circ}C$ , $I_F = -0.9A$ ,	
Reverse Recovery Charge (Note 12)	Q <sub>RR</sub>	_	31	_	nC $di/dt = 100A/\mu s$		
DYNAMIC CHARACTERISTICS (Note 12)							
Input Capacitance	Ciss	_	141	_			
Output Capacitance	Coss	_	13.1	_	pF	$V_{DS} = -50V, V_{GS} = 0V$ f = 1.0MHz	
Reverse Transfer Capacitance	$C_{rss}$	_	10.8	_			
Turn-On Delay Time (Note 11)	t <sub>D(ON)</sub>	_	1.6	_			
Turn-On Rise Time (Note 11)	t <sub>R</sub>	_	2.1	_		$V_{DD} = -50V, I_D = -1.0A,$	
Turn-Off Delay Time (Note 11)	t <sub>D(OFF)</sub>	_	5.9	_	ns	$R_G \approx 6.0\Omega$ , $V_{GS} = -10V$	
Turn-Off Fall Time (Note 11)	t <sub>F</sub>	_	3.3	_			
Total Gate Charge (Note 11)	Qg	_	1.8	_	nC	$V_{DS} = -50V$ , $V_{GS} = -5.0V$ , $I_{D} = -0.6A$	
Total Gate Charge (Note 11)	Qg	_	3.5	_			
Gate-Source Charge (Note 11)	Q <sub>gs</sub>	_	0.6	_	nC	$V_{DS} = -50V$ , $V_{GS} = -10V$ , $I_{D} = -0.6A$	
Gate-Drain Charge (Note 11)	Q <sub>gd</sub>	_	1.6	_		ID = -0.0A	

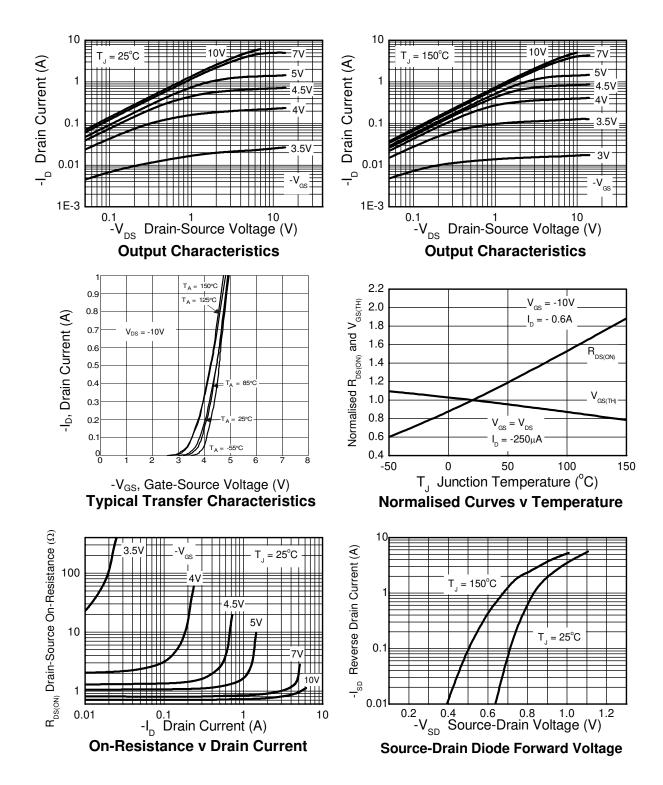
<sup>10.</sup> Measured under pulsed conditions. Pulse width = 300µs. Duty cycle ≤ 2%.

<sup>11.</sup> Switching characteristics are independent of operating junction temperature.

12. For design aid only, not subject to production testing.

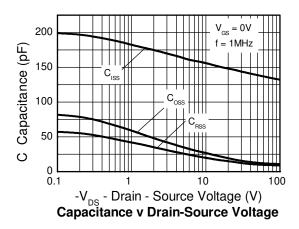


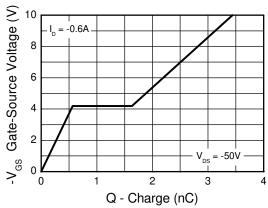
## **Typical Characteristics**





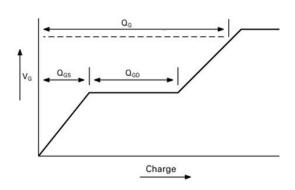
## **Typical Characteristics** (Cont.)



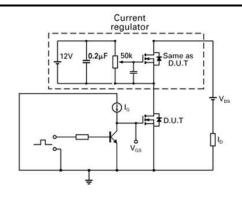


Gate-Source Voltage v Gate Charge

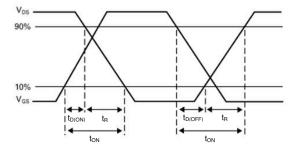
## **Test Circuits**



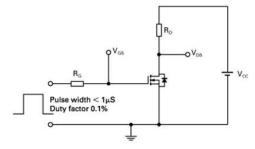
Basic gate charge waveform



Gate charge test circuit



Switching time waveforms



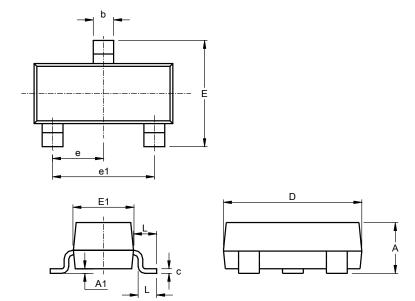
Switching time test circuit



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Type DN)

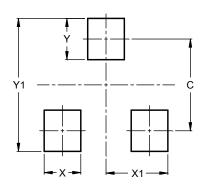


SOT23 (Type DN)				
Dim	Min	Max	Тур	
Α	0.89	1.12	1.00	
<b>A</b> 1	0.01	0.10	0.05	
b	0.30	0.51	0.45	
C	0.08	0.20	0.10	
D	2.80	3.04	3.00	
Е	2.10	2.64	2.42	
E1	1.20	1.40	1.37	
е	0.95 REF			
e1	1.90 REF			
L	0.25	0.60	0.30	
L1	0.45	0.62	0.54	
All Dimensions in mm				

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23 (Type DN)



Dimensions	Value (in mm)		
С	2.0		
X	0.8		
X1	1.35		
Υ	0.9		
Y1	2.9		



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